

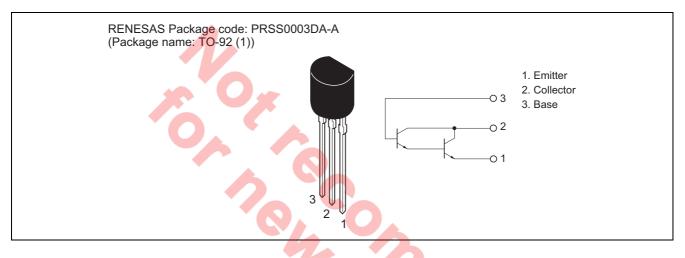
# **2SC1472(K)** Silicon NPN Epitaxial, Darlington

REJ03G0688-0200 (Previous ADE-208-1054) Rev.2.00 Aug.10.2005

### Application

High gain amplifier

### Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	40	V
Collector to emitter voltage	V <sub>CEO</sub>	30	V
Emitter to base voltage	V <sub>EBO</sub>	10	V
Collector current	Ι <sub>C</sub>	300	mA
Collector peak current	i <sub>C(peak)</sub>	500	mA
Collector power dissipation	Pc	500	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

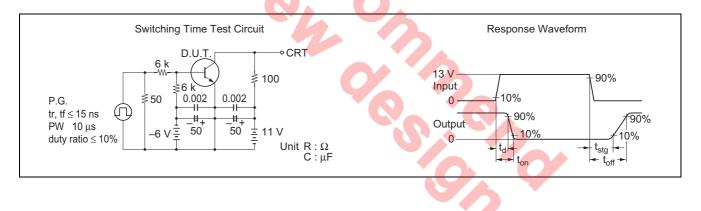


# **Electrical Characteristics**

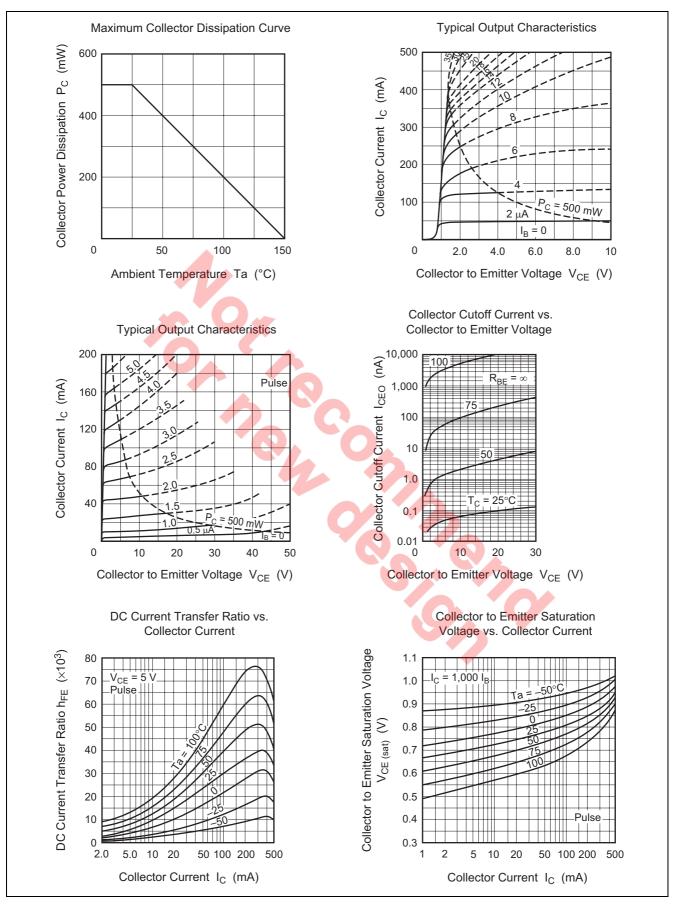
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	30	_	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Collector cutoff current	I <sub>CBO</sub>	—	_	100	nA	$V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	100	nA	$V_{EB} = 10 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE1</sub> * <sup>1</sup>	2000	_	100000		$I_{C} = 10 \text{ mA}, V_{CE} = 5 \text{ V}$
	h <sub>FE2</sub> *1	3000	_	—		$I_{C} = 100 \text{ mA}, V_{CE} = 5 \text{ V}$ (Pulse Test)
	h <sub>FE3</sub> *1	3000		—		I <sub>C</sub> = 400 mA, V <sub>CE</sub> = 5 V (Pulse Test)
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	—		1.5	V	$I_{C} = 100 \text{ mA}, I_{B} = 0.1 \text{ mA}$
Base to emitter voltage	V <sub>BE(sat)</sub>	—	_	2.0	V	$I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA
Gain bandwidth product	f⊤	50		—	MHz	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	—	_	10	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Turn on time	t <sub>on</sub>	_	60	—	ns	$V_{CC} = 11 V$ $I_{C} = 100 I_{B1} = 100 mA$ $I_{B2} = -I_{B1}$
Turn off time	t <sub>off</sub>		800	—	ns	1
Storage time	t <sub>stg</sub>	—	350	—	ns	

Note: 1. The 2SC1472(K) is grouped by h<sub>FE</sub> as follows.

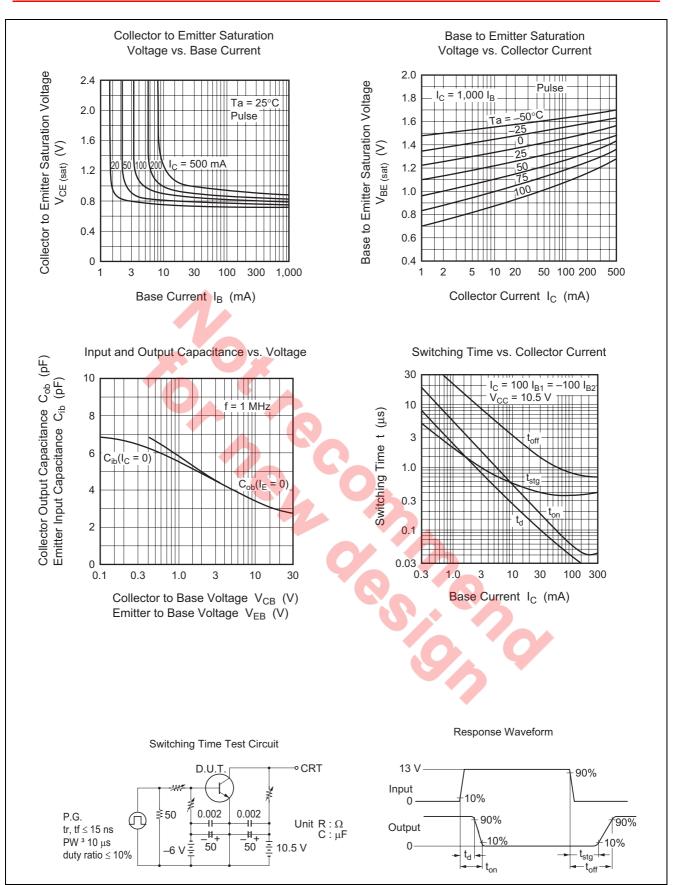
	Α	В	
h <sub>FE1</sub>	2000 to 100000	5000 to 100000	]
h <sub>FE2</sub>	3000 min	10000 min	
h <sub>FE3</sub>	3000 min	10000 min	



### **Main Characteristics**

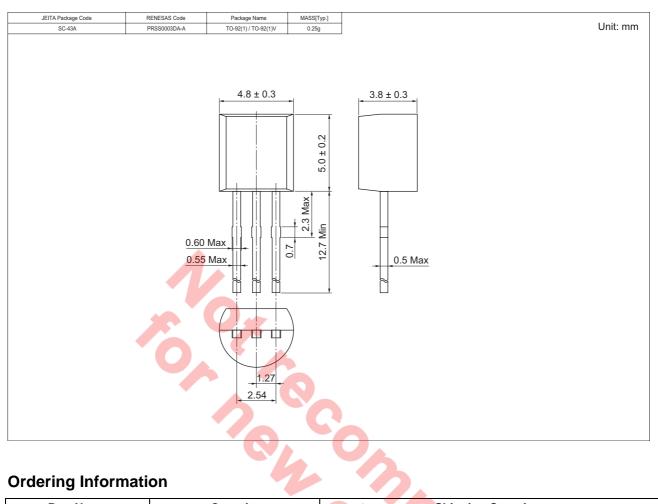






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# **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container
2SC1472KATZ-E	2500	Hold Box, Radial Taping
2SC1472KBTZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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